

0404 INFORMATION DISCLOSURE CITATION

Atty. Docket No.	04329.3299	Application No.	10/829,182
Applicants	Tsutomu SATO et al.		A. WILSON
Filing Date	April 8, 2004	Group:	2819

U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate
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	2000-12858	January 14, 2000	Japan			Abstract
	2001-257358	September 21, 2001	Japan			Abstract
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	2002-324836	November 8, 2002	Japan			Abstract
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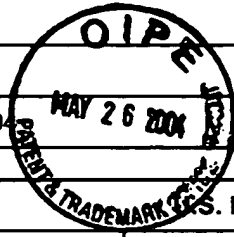
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* No MONTH cited in doc.

INFORMATION DISCLOSURE CITATION

Atty. Docket No.	4329.3299	Appln. No.	10/820,182
Applicant	Sato et al.	Ex. A. Wilson	
Filing Date	April 8, 2004	Group:	Unknown 2815



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0 No	2003-31799	1/31/03	Japan			No	

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Applicants	Tsutomu SATO et al. <i>EX. A. Wilson</i>		
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FOREIGN PATENT DOCUMENTS

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<i>QW</i>	Sato et al., "A NEW SUBSTRATE ENGINEERING FOR THE FORMATION OF EMPTY SPACE IN SILICON (ESS) INDUCED BY SILICON SURFACE MIGRATION", International Electron Device Meeting, pps. 20.6.1-20.6.4, (1999). <i>Dec 1999</i>
<i>QW</i>	Sato et al., "FABRICATION OF SILICON-ON-NOTHING STRUCTURE BY SUBSTRATE ENGINEERING USING THE EMPTY-SPACE-IN-SILICON FORMATION TECHNIQUE", Japanese Journal of Applied Physics, Vol. 43, pps. 12-18, (2004). <i>JAN 2004</i>

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